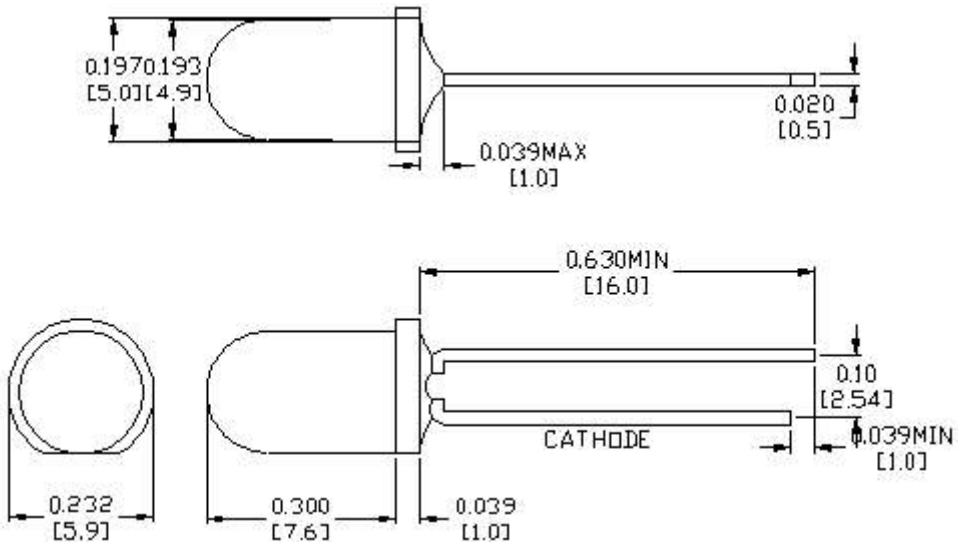
Texas Photonics, Inc.

DESCRIPTION

This is a high speed Silicon detector optimized for applications requiring high Responsivity and a fast response time.

FEATURES

- ❒ High Responsivity
- ❒ High Electrical Bandwidth/Fast response time
- ❒ 5 mm Plastic Package



ABSOLUTE MAXIMUM RATINGS

- ❒ Storage temperature..... -20°C to +85°C
- ❒ Case operating temperature..... 0°C to +70°C
- ❒ Lead solder temperature..... 260°C, 10 seconds
- ❒ Reverse Breakdown Voltage..... 35 Volts

OUTLINE DIMENSIONS

Tolerances are +/-0.005 inches, except as noted
The case is electrically isolated from the pins.

PARAMETER	TEST CONDITION	SYMBOL	MIN	TYP	MAX	UNIT
Capacitance	Vr = 10 V, f = 1 MHz	C		3.0		pF
Open Circuit Voltage	H = 5.0 mW/cm^2	VOC		400		mV
Short Circuit Current	H = 5.0 mW/cm^2	ISC		2		µA
Dark Current	Vr = 10 Volts, H = 0 mW	Id		2	10	nA
Response Time	10%-90%, Vr = 10 Volts R_L = 1K Ω	t_r t_f		6.0 6.0		nsec nsec
Peak Wavelength		λ		940		nm
Electrical Bandwidth	Vr = 5 Volts	BWE		50		MHz
Reverse Light Current	H=5.0 mW/cm^2, Vr=5 V	IL		3.5		µA
Viewing Angle		2 θ1/2		35		Deg

ELECTRO-OPTICAL CHARACTERISTICS (Case T = 25°C)